FAIRCHILD

SEMICONDUCTOR

November 2013

FQP3P20 — P-Channel QFET[®] MOSFET

FQP3P20

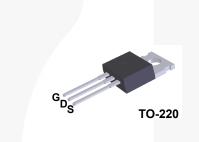
P-Channel QFET® MOSFET -200 V, -2.8 A, 2.7 Ω

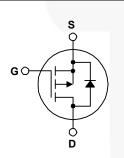
Description

This P-Channel enhancement mode power MOSFET is • -2.8 A, -200 V, $R_{DS(on)}$ = 2.7 Ω (Max.) @ V_{GS} = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 6 nC) resistance, and to provide superior switching performance • Low Crss (Typ 7.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

Features

- I_D = -1.4 A





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

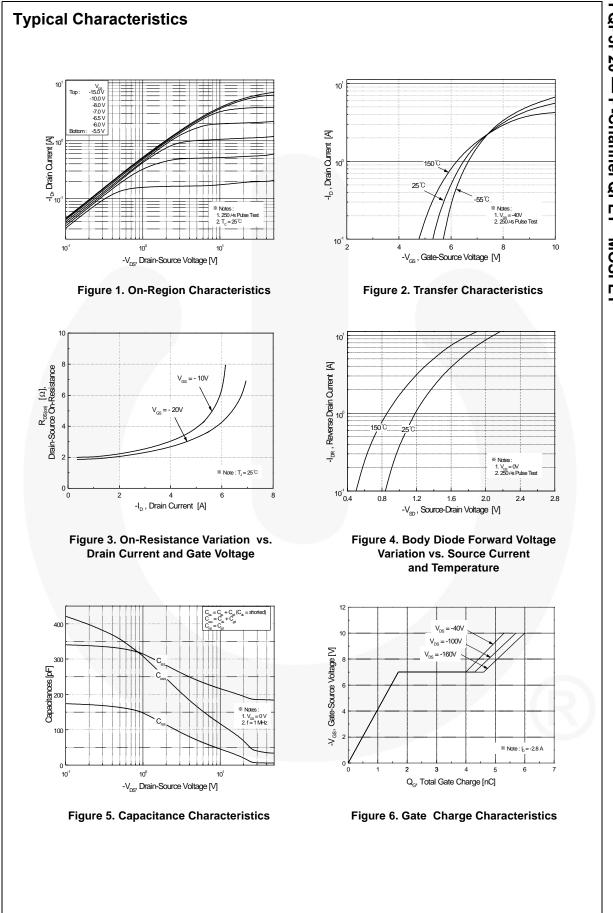
Symbol	Parameter		FQP3P20	Unit	
V _{DSS}	Drain-Source Voltage		-200	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		-2.8	А	
	- Continuous (T _C = 100°C)		-1.77	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	-11.2	A	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	150	mJ	
I _{AR}	Avalanche Current	(Note 1)	-2.8	A	
E _{AR}	Repetitive Avalanche Energy	e Energy (Note 1) 5.2			
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns	
PD	Power Dissipation ($T_C = 25^{\circ}C$)		52	W	
	- Derate above 25°C		0.42	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
Τ _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	

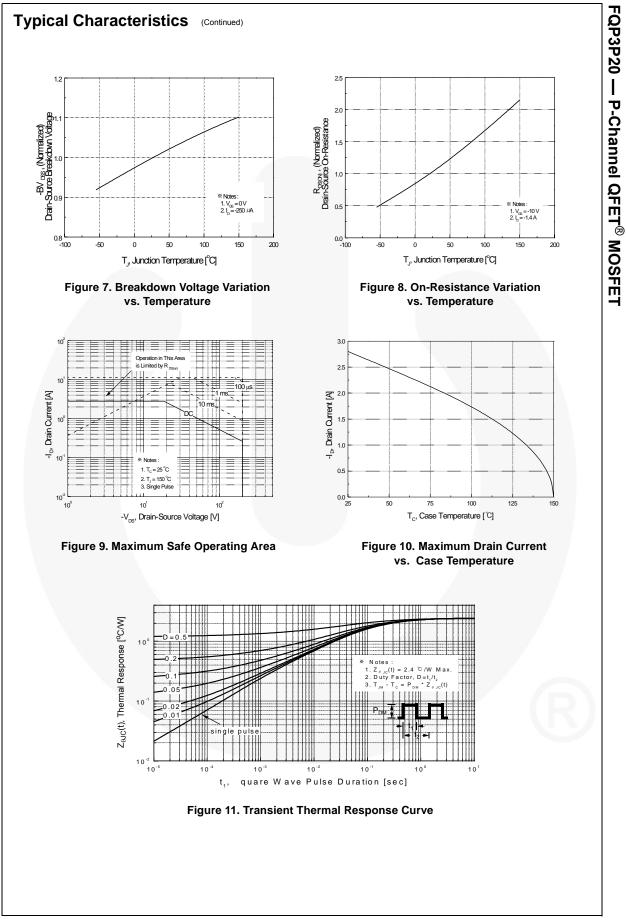
Thermal Characteristics

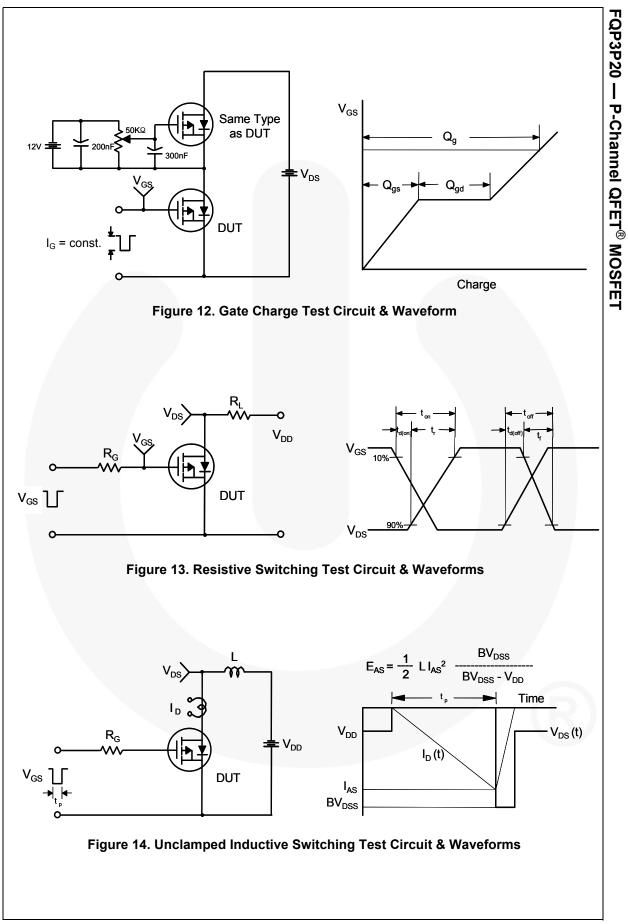
Symbol	Parameter	FQP3P20	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.4	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

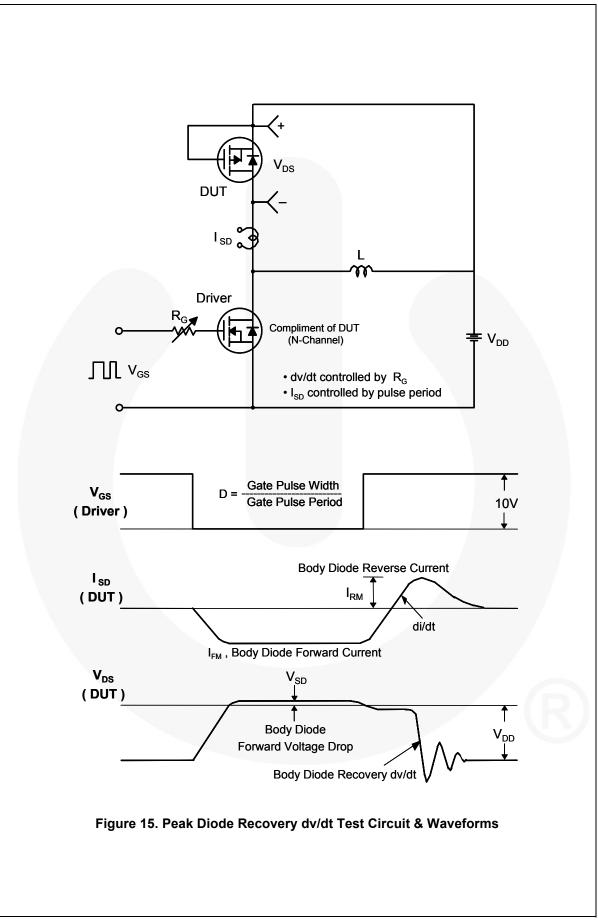
FQP3P20	TO-220	Tuba						
		220 Tube N/		A	N/A		50 units	
cteristics T	_C = 25°C unles	s otherwise noted.						
Parameter		Test Conditions		Min.	Тур.	Max.	Unit	
5								
Breakdown Voltage	age V _{GS} = 0 V, I _D = -250 μA			-200			V	
oltage Temperature	I _D =	I_D = -250 µA, Referenced to 25°C			-0.18		V/°C	
Zero Gate Voltage Drain Current		V_{DS} = -200 V, V_{GS} = 0 V				-1	μA	
		V _{DS} = -160 V, T _C = 125°C				-10	μA	
eakage Current, Forv	-	_S = -30 V, V _{DS} = 0 V				-100	nA	
eakage Current, Rev	erse V _G	$_{\rm S}$ = 30 V, V _{DS} = 0 V				100	nA	
;								
old Voltage	V _D	$_{\rm S} = V_{\rm GS}, \ {\rm I}_{\rm D} = -250 \ {\rm \mu A}$		-3.0		-5.0	V	
Source se	V _G	_S = -10 V, I _D = -1.4 A			2.06	2.7	Ω	
sconductance	V _D	_S = -40 V, I _D = -1.4 A			1.23		S	
ristics								
ance	VDS	_S = -25 V, V _{GS} = 0 V,	V,		190	250	pF	
citance	f =	f = 1.0 MHz			45	60	pF	
sfer Capacitance					7.5	10	pF	
eristics								
y Time		V_{DD} = -100 V, I _D = -2.8 A, R _G = 25 Ω (Note			8.5	25	ns	
Time					35	80	ns	
y Time					12	35	ns	
Time					25	60	ns	
arge	V _D	_s = -160 V, I _D = -2.8 A,			6.0	8.0	nC	
Charge	V _G	V _{GS} = -10 V (No			1.7		nC	
harge					2.9		nC	
e Characteristi	cs and M	laximum Ratings						
ntinuous Drain-Sour		•				-2.8	Α	
						-11.2	Α	
						-5.0	V	
overy Time	-	$V_{GS} = 0 V, I_S = -2.8 A,$ $dI_F / dt = 100 A/\mu s$			100		ns	
					0.34		μC	
lse D SV	ed Drain-Source D iode Forward Volta	ed Drain-Source Diode Forward voltage V _G s ery Time V _G s	ad Drain-Source Diode Forward Currentiode Forward Voltage $V_{GS} = 0 \text{ V}, \text{ I}_S = -2.8 \text{ A}$ ery Time $V_{GS} = 0 \text{ V}, \text{ I}_S = -2.8 \text{ A},$	ad Drain-Source Diode Forward Currentiode Forward Voltage $V_{GS} = 0 \text{ V}, \text{ I}_S = -2.8 \text{ A}$ ery Time $V_{GS} = 0 \text{ V}, \text{ I}_S = -2.8 \text{ A},$	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	ad Drain-Source Diode Forward Current iode Forward Voltage $V_{GS} = 0 V, I_S = -2.8 A$ ery Time $V_{GS} = 0 V, I_S = -2.8 A$, 100	ad Drain-Source Diode Forward Current -11.2 iode Forward Voltage $V_{GS} = 0 V$, $I_S = -2.8 A$ -5.0 ery Time $V_{GS} = 0 V$, $I_S = -2.8 A$, 100	

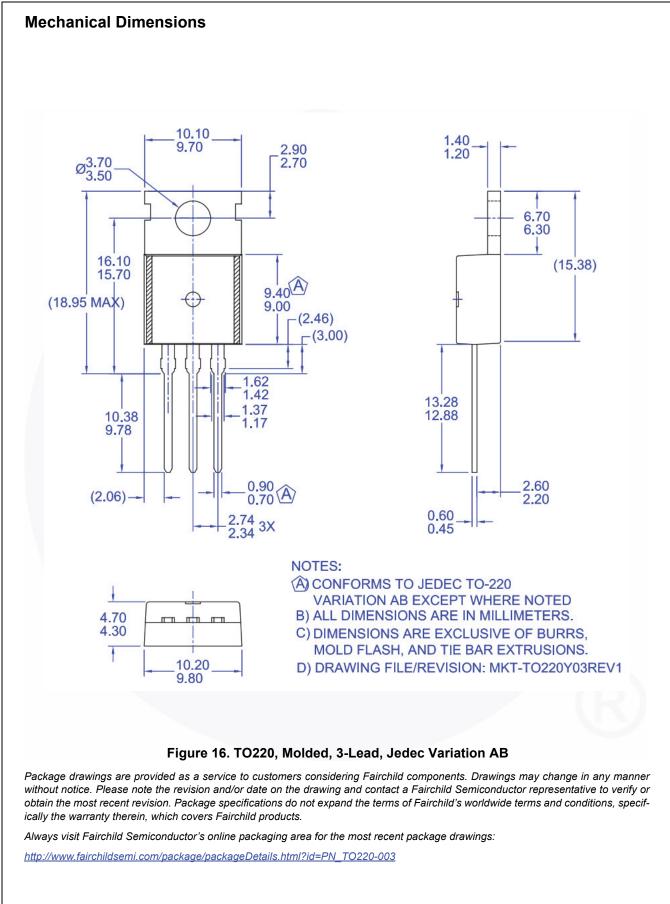
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Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
		Rev. 166

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